

ABSTRACT

In a solid state image pickup apparatus with a photodetecting device and one or more thin film transistors connected to the photodetecting device
5 formed in one pixel, a part of the photodetecting device is formed over at least a part of the thin film transistor, and the thin film transistor is constructed by a source electrode, a drain electrode, a first gate electrode, and a second gate electrode
10 arranged on the side opposite to the first gate electrode with respect to the source electrode and the drain electrode, and the first gate electrode is connected to the second gate electrode every pixel, thereby, suppressing an adverse effect of the
15 photodetecting device on the TFT, a leakage at turn-off TFT, variation in a threshold voltage of the TFT due to an external electric field, and accurately transferring photo carrier to a signal processing circuit.